

Design of a high-quality multi-terminal semiconductor switch

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by

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1

Background

1.1. Introduction

Majorana bound states (MBS) can be used to store quantum information protected from the local environment. MBS can be realised in a hybrid quasi-one dimensional system that combines a strong-spin orbit semiconductor with proximity induced superconductivity. Semiconducting nanowires and two-dimensional electron gases (2DEG) are candidates for creating such devices.

Majorana based quantum computation requires controlled interaction of multiple MBS in a two dimensional device. The ground state evolves following controlled quantum operations by selectively coupling different MBS pairs. Nanowires networks or gate-defined networks in 2DEGs have been studied experimentally and theoretically as platforms for Majorana based computation.

While coupling a single MBS pair can be done using a quantum dot, selective coupling of multiple pairs remains a challenge. On one hand, there are geometrical constraints given by tuning multiple separate nanowires in the topological phase. On the other hand, the coupling of multiple pairs should be optimised simultaneously by the device geometry. Therefore, design and operate a multi Majorana device is a non-trivial task.

The simplest system where multiple MBS can couple non-trivially is in a trijunction geometry. In this thesis we propose a semiconducting cavity connected to three Majorana nanowires that allows for an all-electric controlled interaction between all pairs of MBS.

Initially, the role of geometry is investigated by simulating several cavity geometries and extracting the MBS coupling in the strong coupling regime. We found that the geometrical configuration of the trijunction modulates the coupling of the MBS pairs. Several cavity geometries are analysed, and a triangular cavity with varying angle is found to have the largest coupling for all pairs simultaneously.

Finally, a realistic model is studied via electrostatic simulations of a gate-defined triangular configuration defined on a 2DEG. The non-local nature of the gates makes the nanowire positions crucial in order to recover the effects found for the purely geometric case. The role of each set of gates and the range of voltages used to operate the device are discussed. The electrostatics effects of the gate-defined triangular cavity are analysed and the operational point is described.

1.2. Majorana bound states

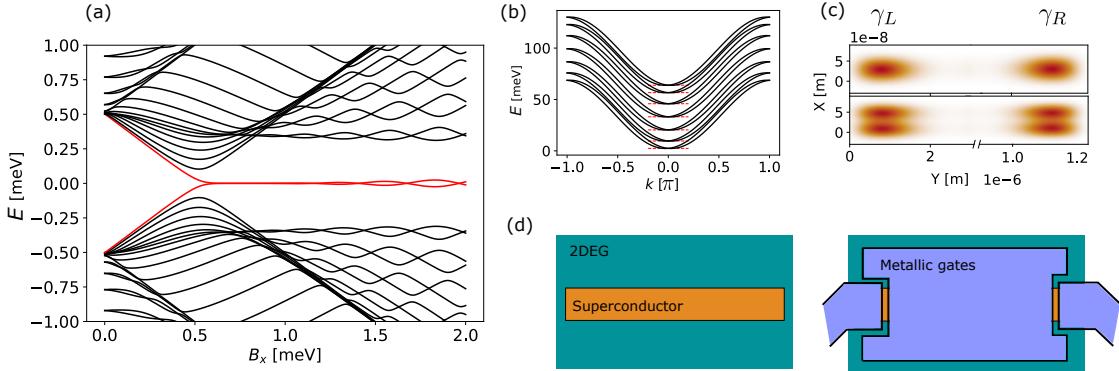


Figure 1.1: Simulations of a Majorana nanowire as described in Eq. (1.4). The following parameters will be used in all simulations: $\Delta = 0.5[\text{meV}]$, $\alpha = 0.3[\text{eV A}]$, and $m^* = 0.023m_e$. Each simulated nanowire has length $L = 120 * a$ and width $W = 7 * a$ where $a = 10[\text{nm}]$ is the lattice constant size. (a) Topological phase transition as a function of Zeeman field B_x . Lowest mode (red) sticks to zero after crossing the critical field. (b) Transverse bands along the translational invariant direction with $\Delta = 0$. The chemical potential is tuned to the bottom of each band (red dashed lines) to create Majoranas. (c) Majorana wavefunctions for the lowest two bands. (d) Illustration of how a Majorana nanowire is built on a 2DEG. Left panel shows the 2DEG with a superconducting stripe on top. Right panel shows the system after the deposition of the gates.

MBS populate the non-local degenerate ground state of a topological superconductor[1]. Under the appropriate conditions, a spinless one-dimensional p -wave superconductor contains two zero-energy excitations that are exponentially localised at the edges of the system. Together, these two zero-energy modes encode a single fermionic mode that can be empty or occupied,

$$f = \frac{\gamma_L + i\gamma_R}{\sqrt{2}}, \quad f^\dagger = \frac{\gamma_L - i\gamma_R}{\sqrt{2}}, \quad (1.1)$$

where $\gamma_i = \gamma_i^\dagger$ are Majorana operators that satisfy $\{\gamma_i, \gamma_j\} = 2\delta_{ij}$.

In a sufficiently long nanowire, MBS are decoupled from each other, and noise sources will interact with each of them individually. The interaction with a single MBS is proportional to a single Majorana operator, i.e. $\gamma \sim f + f^\dagger$, and thus it will change the parity of the system. In a superconductor, however, electrons can only enter or leave as Cooper pairs, which means that the parity is conserved. Therefore, individual MBS are immune to local noise sources.

Consequently, only even powers of Majorana operators are allowed in the Hamiltonian. The simplest allowed term describes the coupling of a pair of MBS. In a single nanowire, or in a linear array of them, it is only possible implement this term with successive MBS. It is given by,

$$H_{pair} = iE_{LR}\gamma_L\gamma_R = E_{LR}(1 - 2f^\dagger f). \quad (1.2)$$

Here, E_{LR} is the tunnelling coupling between the two MBS. Consequently, a general state within the degenerate subspace evolves as,

$$|\Psi\rangle = \alpha|0\rangle + \beta|1\rangle \rightarrow U(t)|\Psi\rangle = \alpha|0\rangle + \beta e^{2iE_{LR}t}|1\rangle. \quad (1.3)$$

However, universal quantum computation cannot be built from using only quadratic fermionic terms as in Eq. 1.2. Controlled interaction between MBS from different fermions

are essential to Majorana based quantum computation[3, 9?]. Therefore, a higher dimensional structure where multiple MBS converge is required in order to do Majorana computation.

1.3. Experimental platforms

MBS can be realised in quasi one-dimensional systems defined on two-dimensional electron gases (2DEGs), or semiconducting nanowires, with strong spin-orbit and in proximity to a superconductor. The Hamiltonian that realises a Majorana nanowire[1] is,

$$\mathcal{H} = \sum_k \Psi_k^\dagger H(k) \Psi_k, \quad H(k) = \left[\frac{|\mathbf{k}|^2}{2m^*} - \mu + \alpha(k_x \sigma_y - k_y \sigma_x) \right] \tau_z + B_x \sigma_x + \Delta \tau_x. \quad (1.4)$$

Here, $\Psi_k^\dagger = (f_{k\uparrow}^\dagger, f_{k\downarrow}^\dagger, f_{k\uparrow} f_{k\downarrow})^T$ are the Nambu spinors in k space, μ is the chemical potential, \mathbf{k} is the 2D wave-vector, α is the spin orbit interaction, B_x is the Zeeman field, Δ is the superconducting gap, and σ and τ are Pauli matrices for the spin and particle-hole basis. MBS appear as zero energy excitations of this Hamiltonian when $B_x^2 \geq \sqrt{\mu^2 + \Delta^2}$.

Realising such material combination is a challenge, and MBS transport signatures are not unambiguous[7, 12]. For example, superconductivity and magnetic fields compete with each other. On the other hand, MBS signatures can be reproduced by states localised in material defects or impurities. Consequently, most of the current work in this field is focused on unambiguously finding a single MBS pair.

Truly one-dimensional systems do not exist. There is a translational invariant direction, and at least one direction with finite width W . The energy of each mode has a contribution from both, and it is given by,

$$E_n(k) = \frac{\hbar^2}{2m^*} \left(k^2 + \frac{\pi^2 n^2}{W^2} \right). \quad (1.5)$$

Here, m^* is the effective mass and the spin orbit splitting is not considered. Independent MBS with different momentum profiles can be formed at each transverse mode when the chemical potential is at the bottom of the corresponding band[8].

1.3.1. Two dimensional electron gases

In order to build a multi Majorana device we require a flexible 2D platform where multiple nanowires can be easily attached. Furthermore, it been shown that properties of Majorana devices can be modulated by changing the device geometry. *2DEGs appear as an interesting platform for since arbitrary geometries can be created using electrostatic gates.* On the other hand, high-quality networks of semiconducting nanowires can be built, but geometries are limited to straight configurations.

Parallel Majorana nanowires are the basic elements for a complex Majorana device. A single nanowire on a 2DEG can be created by adding a superconducting strip on top of the selected region as shown in Fig. 1.1 (d). Then, a top gate is deposited next on top of the device such that depletes the surrounding 2DEG. A narrow quasi-one dimensional channel is created below the superconductor where the gate electric field is screened[5]. Following this procedure, multiple parallel nanowires can be created in a 2DEG by selectively depositing superconducting covers.

There are several Majorana experiments on 2DEGs that have shown promising evidence for scalable and complex devices. Initial experiments[6, 10] focused on characterising the properties of semiconducting layers with a superconducting cover. Advances in material growth allowed for clean interfaces with a hard superconducting gap to develop into the nanowire region. Later experiments focused on tunnel spectroscopy of stripe-like geometries[11] where a zero bias peak (ZBP) was found. However, due to disorder and defects such ZBPs have most likely a trivial origin from Andreev states rather than MBS. Nevertheless, efforts to develop complex devices in 2DEGs are made and new promising materials are being studied.

1.3.2. Electrostatic gates

The potential landscape in a 2DEG can be controlled by deposition of metallic gates on a top layer with an insulating barrier in between that smooths the potential profile[2]. *The electrostatic potential in a 2DEG is found by solving the Poisson equation using a finite elements method on the device geometry.* The potential landscape, $U(\mathbf{r})$, for a given geometrical configuration can be found by solving Laplace equation,

$$\nabla \cdot [\epsilon_r(\mathbf{r}) \nabla U(\mathbf{r})] = 0. \quad (1.6)$$

Here, ϵ_r is the relative permittivity of each layer in the material stack. In general, the quantum electrostatics problem is more complicated due to the interaction of dopant charges with the potential. However, our problem is simpler since no extra charges are required.

1.4. Majorana bound states in a trijunction

In order to create a Majorana qubit, at least three MBS with local pair interactions are required[1]. The device that realises this selective coupling is called a trijunction. It contains two parts: three nanowires, and a central cavity that mediates the coupling. In such a system, demonstration of the simplest non-trivial Majorana evolution experiment can be done.

The geometrical configuration of the trijunction is subject to two main constraints: On one hand, nanowires must be parallel since the topological phase closes for small deviations of the magnetic field. On the other hand, nanowires must have a significant separation from each other such that MBS are well isolated. Consequently, the design of a trijunction geometry with selective coupling between MBS pair is a non-trivial task.

Previous trijunction designs[5] have studied MBS coupling in the tunnelling regime. The trijunction is defined using gates placed on top of a 2DEG, and it is operated by controlling the voltages of the different gates. In this context, the MBS coupling relies entirely on wavefunction overlap along the cavity. Consequently, MBS pairs acquire relatively small couplings with the advantage of not introducing any extra sub gap state.

On the other hand, in the strong coupling the MBS coupling is mediated by cavity states but with extra levels present inside the gap. Nevertheless, the coupling energy of the MBS pairs can become significantly larger, i.e. comparable with the induced gap. The modulation of the coupling now relies on the cavity geometry. Interestingly, it has been shown that properties Majorana devices can be optimised by using geometrical effects. In this context, this work explores the geometrical dependence of selectively coupling multiple MBS pairs in a Majorana trijunction.

2

Trijunction of Majorana nanowires

In this chapter we demonstrate that the coupling of three pairs of MBS in a trijunction is determined by the geometrical details of the central semiconducting cavity. For certain geometrical configurations, a MBS pair couples resonantly with successive cavity states as in the so-called *resonant trapping*, while in other cases the coupling is mediated by individual non-overlapping levels.

We simulate the pair coupling of three Majorana nanowires mediated by a semiconducting cavity using Kwant[4]. For each experiment, a pair of nanowires is set to host MBS in each sub band while the other nanowire is fully depleted. We consider the strong coupling regime where there are no tunnel barriers between the cavity and the nanowires. Furthermore, the phase difference between the selected nanowires is tuned such that the coupling is at a maximum. The coupling energy of each pair is extracted as the value of the lowest non-zero eigenvalue with respect to the cavity chemical potential.

The cavity chemical potential is varied in a range of 4 meV around the first resonance for all cavities. In this range, there are multiple levels that couple resonantly with a given pair of MBS. In order to characterise the coupling, we extract the highest resonance peak for each geometry. Then, we classify them according to their operational robustness, that is, height and width.

2.1. Quasi-one dimensional cavities

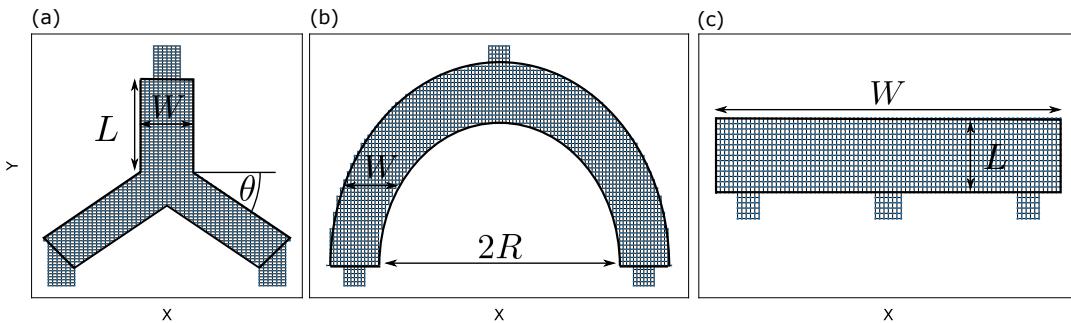


Figure 2.1: Kwant systems describing the three quasi-1D cavities: (a) Y-shaped defined by three parameters: arms length and width, L and W , and lateral arms angle θ . (b) Half-ring defined by the radius R and the width W . (c) Rectangular stripe defined by the length L and width W .

Let us start by building the simplest possible Majorana trijunction. Consider a quasi-1D cavity with mirror symmetry along the y -axis. Then, the position of the three nanowires is fixed: one is attached at the center, and one at each end. Consequently, the phase shift for the central MBS pairs is symmetric around π . Similarly, the coupling of the left-center MBS pair and center-right MBS pair is the same. Under these constraints, we study how the geometry affects the coupling of the two different pairs.

We consider three cavity geometries: In Fig. 2.1 (a) one can observe a Y-shaped cavity. In Fig. 2.1 (b) one can observe a half-ring stripe cavity with three nanowires attached in a fork-like geometry. In Fig. 2.1 (c) one can observe a rectangular stripe cavity with three Majorana nanowires attached.

It is a challenge to build a trijunction that reliably and selectively couples all three pairs of MBS. It is straightforward to couple a single MBS pair in a quasi-1D geometry since the left and right MBS pair will fully enclose the cavity wavefunctions. However, it is a challenge to create a system where the remaining two pairs can couple in a similar way.

2.1.1. Size dependence

Initially, the overall size of the system is varied, and a transition from the small to the long junction regime is found for all geometries. In Fig. 2.2 one can observe the evolution of the largest resonance peak for each geometry as a function of the system size.

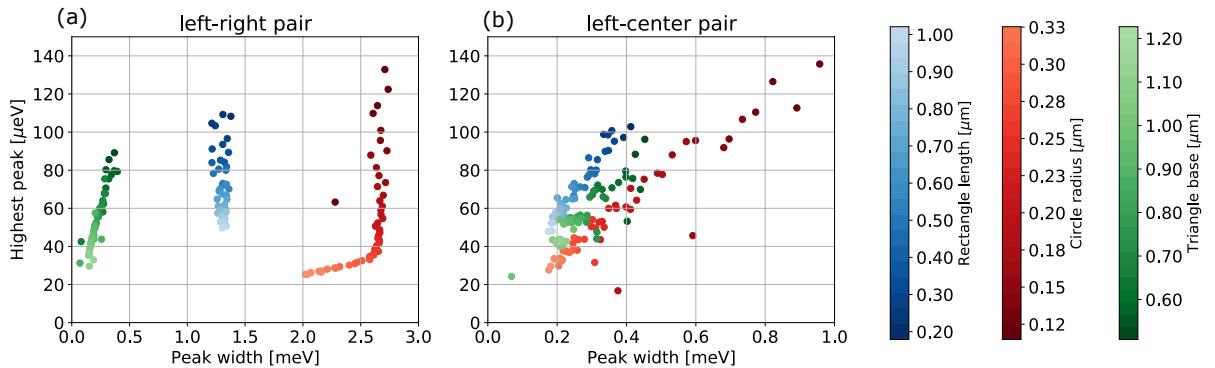


Figure 2.2: Geometrical dependence of the resonant coupling peaks for three quasi-1D geometries that correspond to each colorbar. The system was tuned to the lowest Majorana band. (a) Left-right MBS pair coupling. (b) Left-center MBS pair coupling.

The coupling of the left and right MBS pair shows a clear geometrical dependence as can be observed in Fig. 2.2 (a). Each geometry occupies a separate region in the resonant height-width plane. The ring cavity has the most robust resonant peaks. For small R , the coupling is larger than any other geometry, and it is close to $\Delta/2$. Similarly, the width is the largest, and it persists even for rings with diameter $1 \mu\text{m}$ after which decays. Then follows the stripe geometry that has approximately the same width for all considered widths. Finally, the Y-shaped cavity has overall the smallest resonant peak width.

The coupling of the central MBS pairs, on the contrary, cannot be easily separated for each geometry. Generally, one can see three diagonal stripes in Fig. 2.2 (b) where the stripe geometry has the largest resonant peak height. The peak width decreases as the size increase, and it has the same slope for all geometries. Nevertheless, for sufficiently small sizes, the ring geometry has peak heights and widths larger than any other geometry.

2.1.2. Resonant trapping

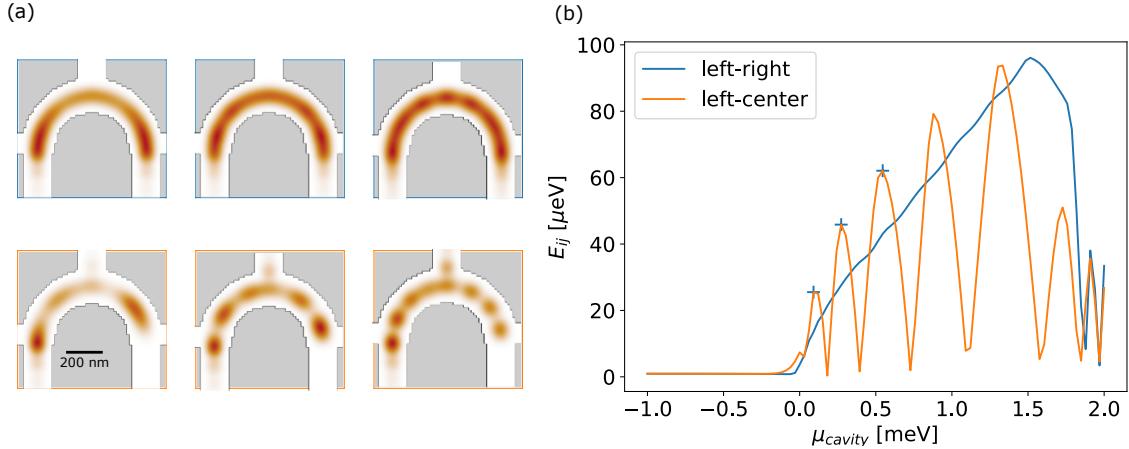


Figure 2.3: Spectra for a half-ring shaped cavity of width $W = 110$ [nm] and radius $R = 300$ [nm]. The system was tuned to the lowest Majorana band. (a) Coupling of each MBS pair. Center-right pair is the same curve as left-center pair. Crosses indicate the positions at where the wavefunction (b) are taken. The color of the frame in (b) corresponds each MBS pair in (a).

Let us consider the half-ring cavity. When the left and right nanowires are close to the ends of the cavity, the MBS pair couple along a sequence of overlapping resonant states as can be seen in the blue line of Fig. 2.3 (a). *The cavity states interfere constructively and the coupling accumulates creating a single wide peak over the resonant region.* It depends crucially on having the lead states around all of the cavity wavefunction as can be seen in Fig. 2.3 (b). This phenomena is known as *resonant trapping*.

For the central pairs coupling, in contrast, a band of resonances cannot form since the cavity wavefunction is not fully enclosed. When coupling the left and central MBS, the cavity region close to the right lead acts as a particle in a box with multiple individual levels that repel each other. Consequently, we observe the orange line shown in Fig. 2.3 (a) where the resonant band is divided in individual resonances.

The difference when coupling multiple MBS pairs relies on the geometric configuration of the cavity wavefunctions and the MBS relative positions. *Then, one can explain the distribution of couplings observed in Fig. 2.2.* The left and right MBS in the ring and stripe geometry have an approximately constant and large widths over the different system sizes because cavity levels remain resonant. On the other hand, the coupling of the central MBS pairs in any geometry has a much smaller width because some part of the wavefunction is not coupled. Particularly, the Y-shaped junction has a small width for all pairs because no resonant trajectories can be created in such geometry.

2.2. Two dimensional cavities

In a ballistic cavity, the motion of the electrons is determined by the shape of the cavity and leads. The electrons follow semiclassical trajectories connecting different leads that can be identified as peaks in the conductance. Following such intuition, we explore if changes in the geometry of a 2D cavity can be used to modulate the coupling of different MBS pairs. Particularly, we explore how the angular dependence of the incoming modes, and internal angles of the cavity, influence the MBS coupling.

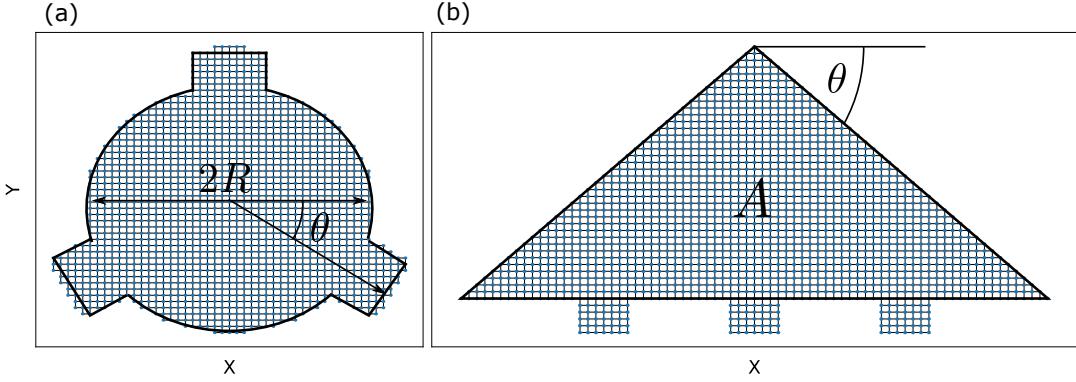


Figure 2.4: Left: Kwant system of a half-ring shaped cavity. It is defined by the radius R and the width W . Thinner rectangular segments represent the positions of the Majorana nanowires attached. Right: Lowest four eigenstates of the cavity with the nanowires fully depleted.

We consider three geometries: In Fig. 2.4 (a) one can observe a circular cavity with Majorana nanowires attached in a fork-like geometry. In this geometry one can control the angle of the incoming MBS. In Fig. 2.4 (b) one can observe a triangular cavity with nanowires attached at the lower side. In this geometry one can control the angle of MBS scattering within the cavity by changing the diagonal sides. In order to explore the role of the positioning of the leads, we explore a variation of the triangular geometry with the central lead in the top side. Lastly, we consider a rectangular geometry that can be created by extending the length of the stripe geometry shown in Fig. 2.1 (c).

2.2.1. Size dependence

Let us start by discussing the size dependence of the cavities. In Fig. 2.5 one can observe the size dependence of the resonant peak for the three two-dimensional geometries.

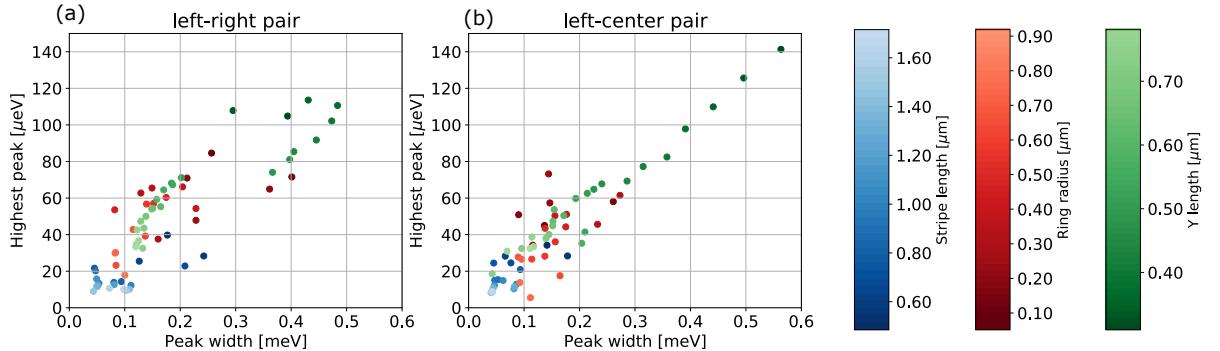


Figure 2.5: Size dependence of the three 2D geometries considered in this section corresponding to each colorbar. The system was tuned to the lowest Majorana band. The (a) left right and (b) left center largest resonant peaks are shown. The angle of all the cavities here is $\theta = \pi/4$.

Overall, there is no major distinction between the coupling of different pairs. All couplings decay as the system size increases following a diagonal line in panels (a) and (b). Nevertheless, the geometry dependence can be seen in three different regions along the diagonal.

On the rightmost region, one observes that the triangular geometry has the largest couplings and widths for small sizes. Descending along the diagonal, the triangular and cir-

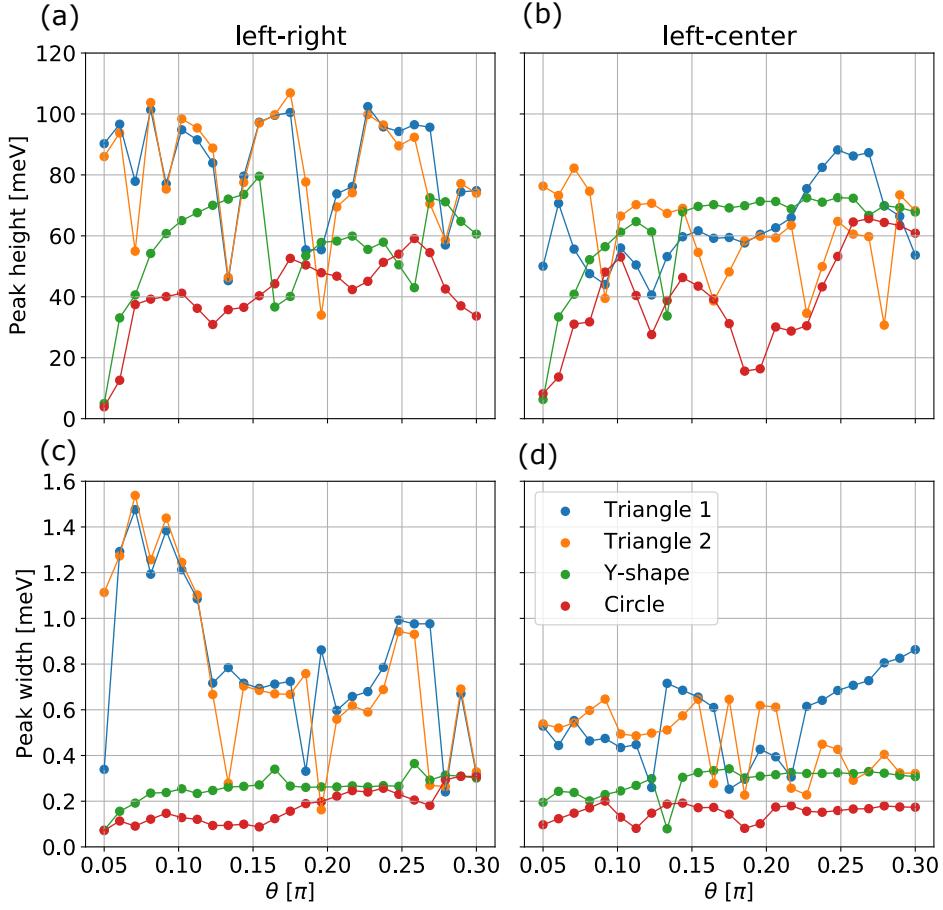


Figure 2.6: Angular dependence of the resonant coupling peaks for four geometries with angle dependence. The system was tuned to the lowest Majorana band. Peak height and width for (a, c) left-right MBS pair and (b, d) left-center MBS pair coupling. The area of the triangular cavities was $A = 900 \text{ [a}^2\text{]}$. The radius of the circular cavity is $R = 250 \text{ [nm]}$. The size of the Y-shaped cavity is similar to that of the triangular cavity.

cular geometries overlap. Remarkably, there is a significant size difference between them in the overlapping region, approximately 500 nm. Most of circular geometries are concentrated in this region. At the bottom of the diagonal, one observes that the worst MBS couplings happen for rectangular geometries.

2.2.2. Angular dependence

The angle is changed in two triangular cavities, one circular cavity, and the Y-shaped cavity. The resulting coupling for each pair and geometry is shown in Fig. 2.6.

The triangular geometry shows a transition from the resonant trapping regime to the single resonance regime while maintaining an approximately constant peak height. One can observe that the peak height stays around the same value for a large range of angles in panel (a). This behaviour is present in both triangular geometries as one can observe the overlap between orange and blue dots. As expected, the position of the central lead does not influence the coupling of the left and right MBS. The width, shown in panel(c), shows a more complicated behaviour. Initially, it is significantly larger than any other system, but later it decreases. Around $\theta = \pi/4$, the width reaches 1 meV.

In order to understand this behaviour, let us observe that for small angles the triangular

cavity resembles a quasi-1D system. By cutting the edges of the stripe geometry, the wavefunction is concentrated towards the center such that it can be easily trapped between the left and right leads as observed in the blue curve of Fig. 2.7 (b). As the angle increases, the resonant band splits into several sub bands that contain a few resonances each as observed in Fig. 2.7 (a). If the angle increases further, these resonances fully split into individual levels, thus explaining the saturation found in Fig. 2.6 (c).

The coupling of the left and central MBS pair -on the contrary- is more complicated to analyse due to the high overlap between geometries as observed in Fig. 2.6 (b) and (d). Couplings for both triangular geometries are around the same region in width and height for small angles. As the angle increases, the width of the configuration with central lead at the lower side (blue) increases, while the other configuration (red) decreases.

It is remarkable that the triangular geometry has two configurations that can be used to operate a Majorana trijunction with similar coupling magnitude and width for all MBS pairs. These two configurations are shown in Fig. 2.7. Note, however, that the small angle configuration would be rather considered a quasi-1D system since the ratio between its dimensions. That is the reason why the resonant band has such a large width and encloses many states. Nevertheless, resonant trapping is still present in the second configuration, but with fewer states inside the resonant band.

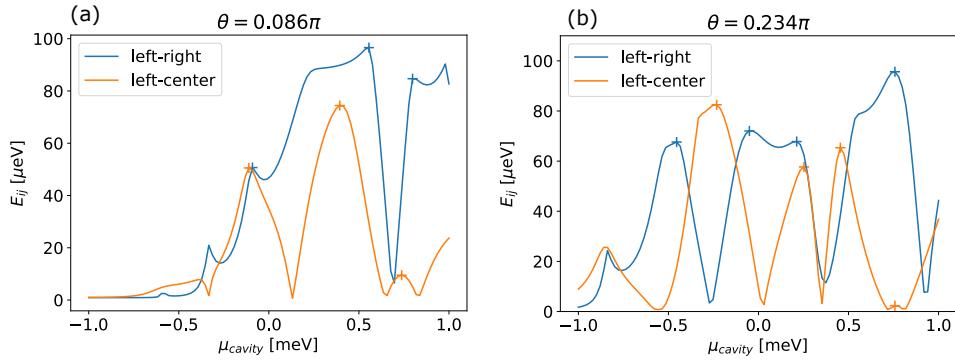


Figure 2.7: Coupling of triangular geometries with the central lead at the (a) top and (b) bottom sides. The total area of the triangle is $A = 1200 [\alpha^2]$.

For the remaining geometries, there is indeed a modulation for the left and right MBS pairs. The overall coupling is comparable to the triangular geometries, but the width is much smaller. Interestingly, the left and central MBS coupling for the Y-shaped cavity converges to a peak height of about 70 meV as the angle increases (see Fig. 2.6 (c) green points). The circular geometry shows that different angles enhance the coupling of different pairs as can be seen in the red lines.

2.2.3. Majorana sub bands

By tuning each nanowire sub band into the topological phase, we probe the momentum distribution of the cavity states. In Fig. 2.8 one can observe the mean coupling for each band. It has been averaged over all geometrical configurations and all MBS pairs since no clear distinction between them was found.

Overall, the coupling decays exponentially as the band index increases. The decay is modulated by the geometry, but the trend holds in all cases. There is, approximately, two order of magnitude decrease in the coupling from the lowest to the highest band.

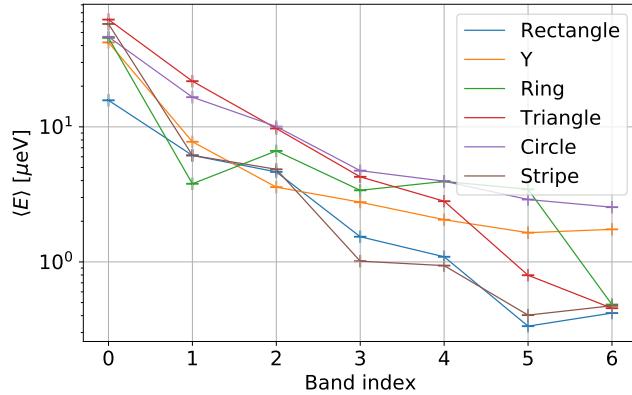


Figure 2.8: Mean geometry-pair coupling for all Majorana sub band and all geometries considered in this section. The geometry average was taken over the data shown in Fig. 2.5.

The lowest band carries the largest coupling. This allows us to infer that the momentum distribution of cavity states is dominated by low momentum states. This is reasonable since the coupling of spatially separated MBS requires delocalised cavity states. However, a precise quantitative description of the momentum profiles inside the cavity goes beyond the scope of this work.

3

Gate defined triangular cavities

In this chapter, we simulate a gate defined triangular cavity and describe its operation as a switch that couples different MBS pairs. The device is built using a stack with three layers of materials: 2DEG, dielectric and metallic gates. The electrostatic potential inside the 2DEG is found as the solution to Eq. (1.6) using the finite element solver from Ref. .

Two devices are simulated in order to study the angular dependence previously found. First, we discuss the tuning of each device such the potential resembles the triangular cavity and the nanowires are strongly coupled. Then, the MBS coupling is calculated and compared to the purely geometric case.

3.1. Gates configuration

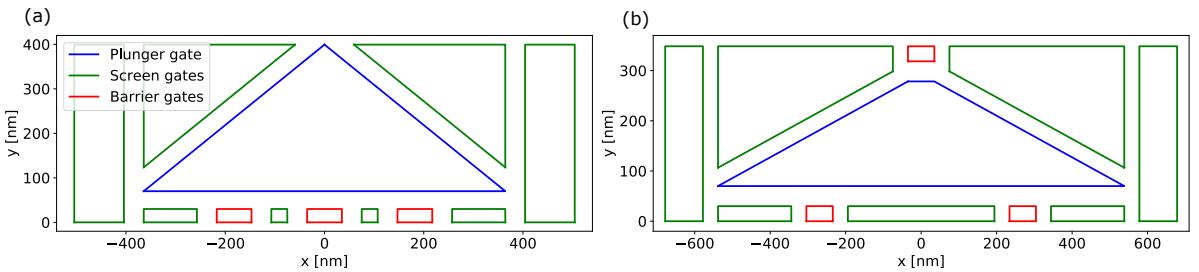


Figure 3.1: Gate configuration of the two triangular cavities considered. The area is set $A = 1200 \text{ [a}^2\text{]}$. (a) Triangular cavity with angle $\theta = 0.234\pi$ with all nanowires at the lower side. (b) Triangular cavity with angle $\theta = 0.125\pi$ with central nanowire at the top side. Spacing between gates is set to 40 nm. Barrier gates have length 30 nm and width 70 nm. Nanowires (not shown) are attached at the ends of the barrier gates. The vertical configuration includes a 2DEG of thickness 40 nm. Then follows an insulating layer of thickness 40 nm, and finally the metallic gates of thickness 60 nm.

A trijunction is a complex Majorana device that can be implemented on a 2DEG by selectively depositing electrostatic gates. It contains two main regions: three nanowires and a semiconducting cavity. We focus on the design of a gate defined triangular cavity. We do not consider the electrostatic modeling of the nanowires since one can assume that the electric field in the nanowires is screened by the superconductor.

The gates are placed in a single layer above the 2DEG with a dielectric layer in between. Different layer configurations were explored, and a single layer was found to be the best in terms of shape-resolution and voltage range. The thickness of each layer determines

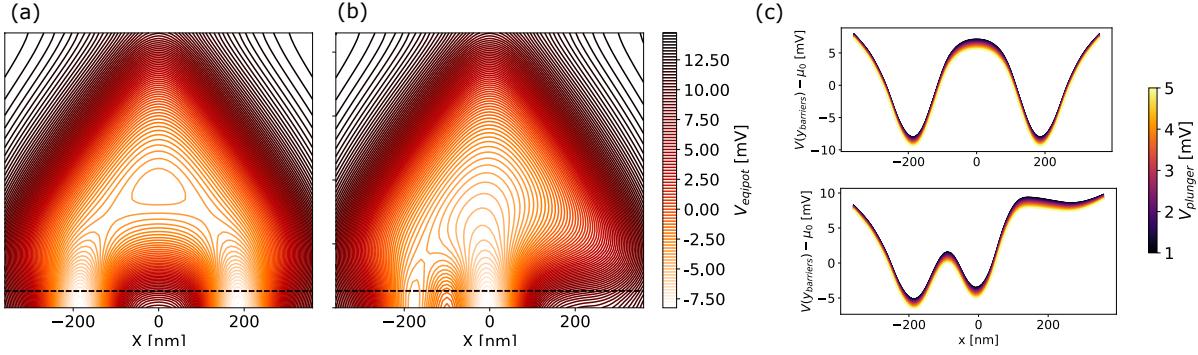


Figure 3.2: Equipotential lines inside the device for representative parameters of the (a) left and right MBS pair and (b) left and center MBS pair. Colorbar indicates value of equipotential lines. (c) Cut of the potential along the tunnel barriers, i.e. dashed black lines in (a) and (b), taken for a range of plunger gate voltages. Colorbar in (c) indicates the plunger gate voltage.

how much the electric field penetrates into the 2DEG. We consider typical parameters from experiments as described in the inset of Fig. 3.1.

In contrast to the geometrical model discussed in the previous chapter, the trijunction is defined in a smooth potential landscape. The global potential is affected by all involved gates. There are three kinds of gates:

1. Plunger gate: Defines and controls the potential inside the triangular cavity region.
2. Screen gates: There are two kinds of screen gates: First, the triangular screen gates deplete the 2DEG around the plunger gate, which contributes to the overall triangular shape. Second, the screen barrier gates between the tunnel gates that keep each nanowire channel separated from the others.
3. Barrier gates: Modulate the coupling between each nanowire and the cavity. They allow to tune the system in the insulating, tunnelling, and strong coupling regimes.

In general terms, to operate the device optimally we require the minimum number of tunable gates while having enough flexibility to connect different MBS pairs. There are two basic requirements that must be satisfied at all times:

1. Electron density inside the cavity is placed under the plunger gate.
2. Selectively couple different pairs of MBS via the cavity by tuning the barrier gates. The last MBS remains decoupled.

These two requirements require us to calibrate the tunnel and the screen gates separately. At the same time, one has to vary the minimum number of gate voltages while maximising the coupling. In the remaining of this section, we discuss how these conditions can be satisfied in both devices.

3.2. Device 1

In this section we describe the operation of the gate configuration shown in Fig. 3.1 (a). Interestingly, this device allows us to explore geometric deformation beyond the triangular

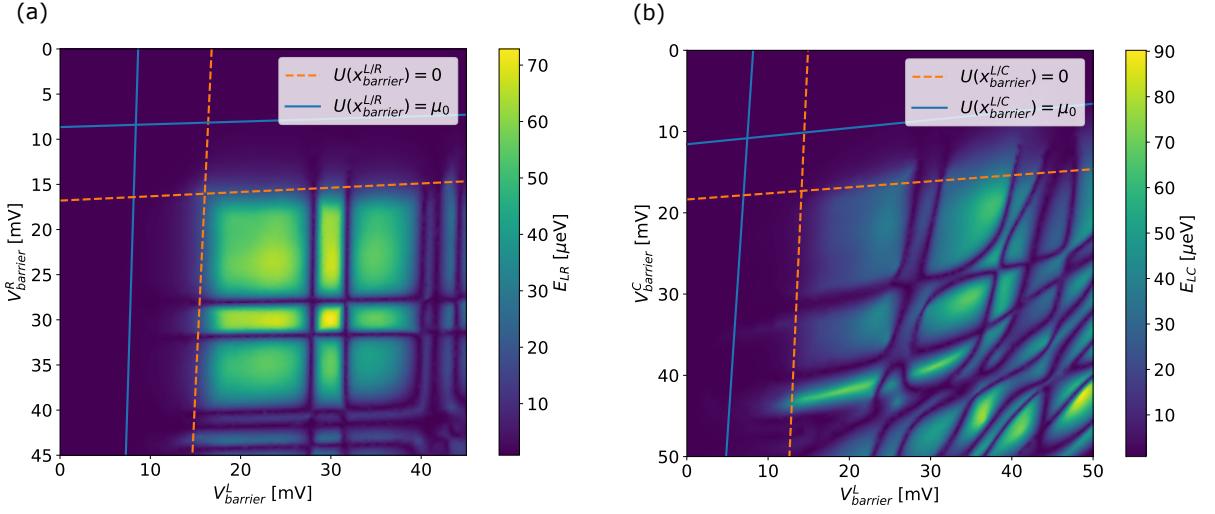


Figure 3.3: Coupling of (a) left and right MBS pair and (b) left and central MBS pair as a function of the corresponding barrier gates. Orange and blue lines indicate when the potential at the bottom of the barriers crosses 0 V or the MBS potential, μ_0 . Plunger gate is tuned around the first resonance. Gate voltages used correspond to those described in Table 3.1.

cavity by tuning the triangular screen gates. In Fig. 3.3 (a) - (b) one can observe the potential inside the 2DEG for the coupling of each pair. One can observe that the triangular walls are well defined in the potential, but inside the triangle the bottom of the potential has a different shape.

In Fig. 3.3 (c) one can observe that a double well is created when coupling a given pair of MBS. For the left and right MBS pair (upper panel) the potentials remain well separated. On the other hand, the central pairs are very close and the screen barrier can be lowered below the MBS potential, allowing for direct coupling. To explore potential deformations it is required that the tunnel channels to the nanowires remain separated.

3.2.1. Nanowire channels

Operating the left and right tunnel barriers is straightforward since they are far from each other. Consequently, there is no interdependence between them as can be observed in Fig. 3.3 (a). On the other hand, the operation of the central pairs is not symmetric given the mutual influence of successive barrier gates. In Fig. 3.3 (b) one can observe that the slope of the potential crossings suggests a mutual interaction between successive barrier gates.

The system can be tuned in the insulating, tunnelling, and strong coupling regimes by manipulating the barrier gates. The blue and orange lines in Fig. 3.3 indicate the value of the potential at the bottom of the barrier gates with respect to μ_0 and 0, respectively. The insulating regime corresponds to the region beyond the blue lines. The tunnelling regime starts at the blue line, when the barrier potential crosses μ_0 . In this regime, the coupling is mediated by direct overlap of the MBS wavefunctions. Therefore, one observes a difference in the tunnelling regime of panels (a) and (b) since in the later the MBS are closer. The orange lines indicate the start of the strong coupling regime.

As the barriers are lowered, there are two new effects: On one hand, new crossings caused by resonant cavity levels appear. On the other hand, for very large barrier gates, the MBS couple directly since the screen barrier is lower than μ_0 . The former effect can be seen clearly in panel (a) as the two crossings in the strong coupling regime. The latter can

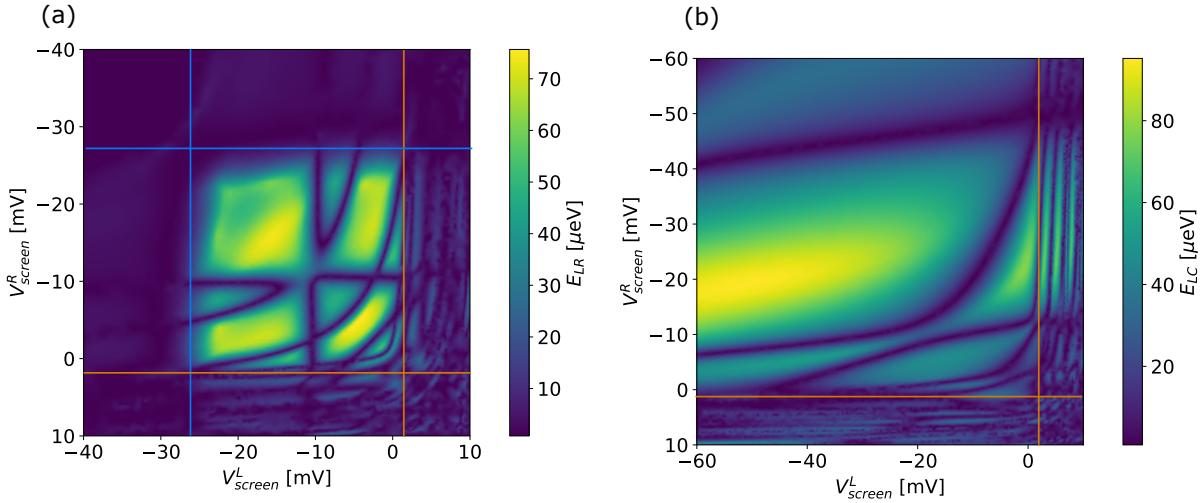


Figure 3.4: Coupling of (a) left and right MBS pair and (b) left and central MBS pair as a function of the triangular screen gates. Three regimes of the electron density localisation are separated by the orange and blue lines. Plunger gate is tuned around the first resonance. Gate voltages used correspond to those described in Table 3.1.

be seen in the lower right part of panel (b) where the coupling increases due to direct coupling. Keeping the barrier potential as small as possible within strong coupling decreases the influence of these effects.

3.2.2. Background potential

The screen gates depleted the electronic density in the 2DEG such that is concentrated below the plunger gate. In Fig. 3.4 one can observe the MBS coupling as a function of the voltages of the two triangular screen gates for each pair. First, one observes that below the orange lines, there some resonances with a small MBS coupling. In this case, the density is not confined under the plunger gate, but electrons can move over the whole 2DEG. By tuning the potential to more negative values, between the orange and blue lines, a region with large coupling develops, indicating that electrons are confined in the triangular region. Further increasing the potential depletes the area under the plunger gate as can be seen beyond the blue line. Observe that it takes higher voltages to reach this last regime in the case of panel (b).

In panel (a) one observes that the case of the left and right MBS pair is symmetric. On the other hand, panel (b) shows an asymmetry for the left and central MBS pair. Here the coupling increases by tuning one screen gate more negative than the other. This is new regime for the coupling of the central MBS pairs that was not found in the purely geometric model. One can understand this phenomena as an effectively size decrease for the cavity. As the right screen gate increases, the left and central MBS overlap increases as can be observed.

3.3. Device 2

In this section we describe the operation of the gate configuration shown in Fig. 3.1 (b). In contrast to the previous device, here the interplay between barrier and screen gates is crucial to keep the nanowires connected to the cavity. In Fig. 3.6 (a) - (b) one can observe

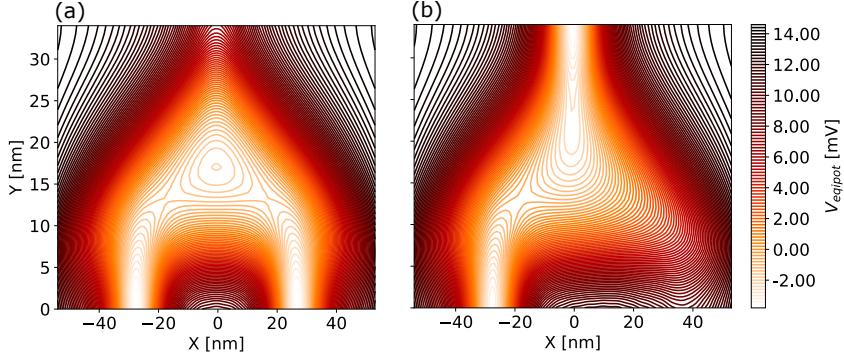


Figure 3.5: Equipotential lines inside the device for representative parameters of the (a) left and right MBS pair and (b) left and center MBS pair. Colorbar indicates value of equipotential lines. (c) Cut of the potential along the tunnel barriers, i.e. dashed black lines in (a) and (b), taken for a range of plunger gate voltages. Colorbar in (c) indicates the plunger gate voltage.

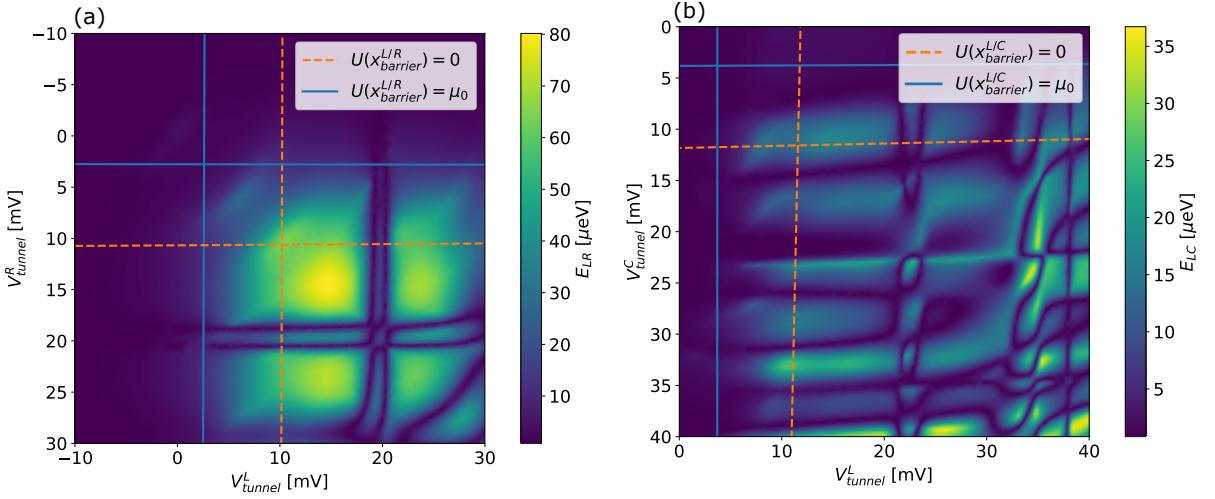


Figure 3.6: Coupling of (a) left and right MBS pair and (b) left and central MBS pair as a function of the corresponding barrier gates. Plunger gate is tuned around the first resonance. Gate voltages used correspond to those described in Table 3.2.

the potential inside the 2DEG for connecting each pair. One observes that the barrier gates are well separated from each other, but the electron density below all of them depends in the surrounding screen gates as in the case of the top barrier in panel (b).

Since this device has a smaller angle, it resembles a quasi-one dimensional shape. Observe that it is 800 nm long and 150 nm wide. The wavefunctions will concentrate around the center of the cavity and not in the narrow edges. Consequently, one can expect a larger coupling in the tunnelling regime, and resonant trapping for the left and right MBS coupling. Furthermore, in panel (b) one can observe that the potential minima inside the cavity follows a narrow channel trajectory. The far disconnected end of the triangular potential is higher, which implies a large deformation from the geometrical case.

3.3.1. Nanowire channels

There are two differences with respect to the previous device: First, since all barrier gates remain well separated from each other, there is no interdependence of barrier gates for any pair as one can observe in Fig. 3.6. Second, in the tunnelling regime, there is a significant

coupling. This is a consequence of how the gate geometry influences the spatial distribution of the wavefunctions. In this device, the wavefunction concentration in the middle of the cavity is higher than in the previous device.

In the strong coupling regime there is a large difference between the coupling of the different pairs. One can observe that panel (a) is similar to the previous device, which suggests that the triangular geometry effects are present in both devices. On the other hand, panel (b) shows a smaller coupling in contrast to the purely geometric model. This difference arises from the new structure of the cavity created by the gates. Furthermore, a new set of resonances appears with a non-trivial dependence in both tunnel barriers.

3.3.2. Potential background

As in the previous device, the coupling is larger when the electron density is below the plunger gate than when it is delocalised over the 2DEG. One can observe this in the separate regions shown in 3.7 marked by the blue and orange lines. In panel (a) one observes that there is a region where the coupling for the left and right MBS pair has a series of resonances. By tuning the screen gates inside one of them, the magnitude of the coupling is similar to the previous device.

As mentioned before, the position of the barrier gates is modulated by the screen gates. Therefore, if the later are not tuned correctly, the nanowires will disconnect from the cavity. This configuration can be observed in panel (b) above the blue line. One observes a similar pattern than in panel (a), but deformed towards more negative left screen gate voltages. On the other hand, if the potential of the right screen triangle gate is beyond the blue lines, the coupling of the left and central pair vanishes. The region below the orange lines indicates that there is a non-zero coupling for when the electron density is delocalised over the 2DEG, but no distinguishable pattern can be observed.

In this device is possible to reach a maximum coupling by tuning the electron density to be under the plunger gate. However, there is a difference of about 30 meV for the coupling of different pairs. The gates design does not allow to explore cases beyond the triangular cavity as in the previous device. In fact, tuning of the screen gates is required for each pair to operate properly.

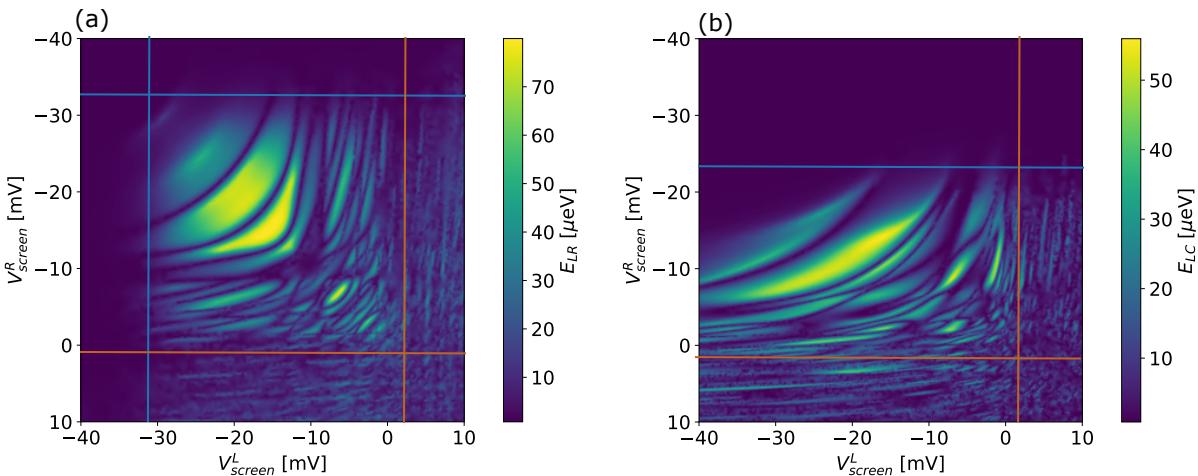


Figure 3.7: Coupling of (a) left and right MBS pair and (b) left and central MBS pair as a function of the triangular screen gates. Plunger gate is tuned around the first resonance. Gate voltages used correspond to those described in Table 3.2.

3.4. Devices operation

In the previous discussion we have described the optimal point for operating each the devices considered. In this section we tune the devices to the operational point, and calculate the MBS coupling. In Fig. 3.8 one can observe the coupling of all relevant MBS pairs for each device. By observing panel (a) we can see that the coupling of the different MBS pairs is close to the maximum coupling around $V_{plunger} = 2\text{meV}$ for the first device. On the other hand, panel (b) shows that the coupling of different pairs in the second device is highly asymmetric. A maximum can be found for all pairs around $V_{plunger} = 6.5 \text{ meV}$.

Interestingly, the shape of the spectra for both MBS pairs in device 1 (a) is similar, but the central pair has a larger level spacing. This support the idea that the deformation of the triangular cavity leads to an effective size reduction that involves only the relevant pairs. On the other hand, for the second device, the peak in the coupling of the left and right pair is anticorrelated with that of the left and central pair.

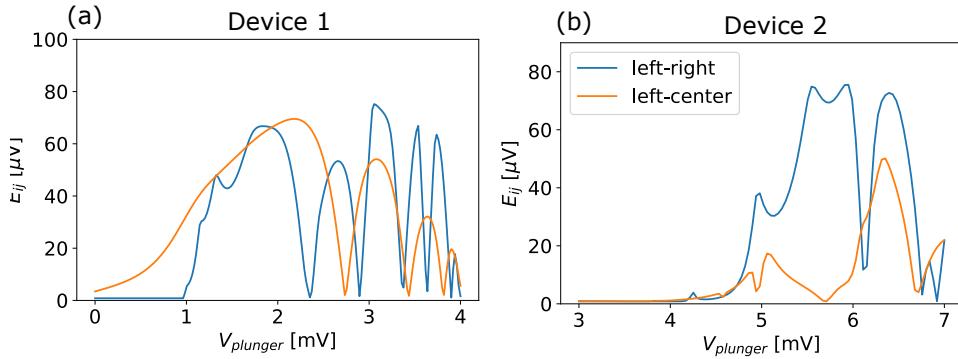


Figure 3.8: MBS coupling of all relevant pairs for each device tuned accordingly to the parameters described in Table 3.1 and Table 3.2.

Both devices are operated by changing three gate voltages to tune between each MBS pair. First of all, the barrier gates are required to connect or disconnect nanowires from the cavity. Tuning between different pairs requires to disconnect one wire while connect a new one. This is required in all devices and the voltage difference is the largest. On the other hand, the screen gates are tuned such that the electron density is inside the cavity and the MBS coupling is optimal. Based on the discussion from the previous sections, the set of gate voltages that define the operational point of the device are shown in Table 3.1 and Table 3.2.

| | $V_{barrier}^L$ | $V_{barrier}^R$ | $V_{barrier}^C$ | V_{screen}^L | V_{screen}^R |
|--------------|-----------------|-----------------|-----------------|----------------|----------------|
| left-right | 35 | 35 | -20 | -15 | -15 |
| left-center | 35 | -20 | 20 | -15 | 40 |
| center-right | -20 | 35 | 20 | 40 | -15 |

Table 3.1: Gate voltage configuration used for coupling different MBS pairs. Voltage units are *meV*. Remaining gate voltages are fixed: screen barriers between nanowires -30 meV , screen barriers around nanowires -15 meV .

| | $V_{barrier}^L$ | $V_{barrier}^R$ | $V_{barrier}^C$ | V_{screen}^L | V_{screen}^R |
|--------------|-----------------|-----------------|-----------------|----------------|----------------|
| left-right | 17 | 17 | -20 | -15 | -15 |
| left-center | 17 | -20 | 17 | -10 | -20 |
| center-right | -20 | 17 | 17 | -20 | -10 |

Table 3.2: Gate voltage configuration used for coupling different MBS pairs. Voltage units are *meV*. Remaining gate voltages are fixed: screen barriers between nanowires -30 meV, screen barriers around nanowires -15 meV.

4

Conclusions

In this work we have demonstrated that the question of designing a trijunction of Majorana nanowires is non-trivial. We have not answered the question of what is the optimal geometry, but we have made progress by analysing different geometries in 1D and 2D.

We have found a systematic difference between different cavity geometries. In quasi-1D cavities, there is a clear behaviour of the different geometries considered. On the other hand, 2D systems show a complex behaviour where device size and shape influence the coupling and shape resolution. Overall, the ring and the triangular geometry are the most interesting candidates in terms of resonance peak height and width.

The implementation of a gate-defined trijunction requires a systematic tuning of the device. We have found that the geometric description holds for two-dimensional shapes. However, as the system size decreases, electrostatic effects play a major role that diverges from the geometrical description. Interestingly, further optimisation of the coupling can be achieved by controlling the shape of the potential with multiple gates.

This work can be extended in two possible ways: On the one hand, further geometry analysis can be used to find the optimal cavity shape that will be later implemented with an electrostatic model. On the other hand, include a measurement protocol that allows to measure the state encoded by the MBS. This is a necessary ingredient in order to design a Majorana qubit.

The implementation of a gate-defined ring geometry remains as an open question. The main problem that we found with this geometry is that the coupling between different pairs is highly asymmetric due to resonant trapping. Nevertheless, this problem can be circumvented by defining multiple regions along the ring that can be activated or depleted depending on the pair to couple.

Another possible extension is to implement an optimisation algorithm that determines the optimal shape of the cavity. To consider all pairs simultaneously, one can optimise the minimum coupling. This thesis can be used to establish the constraints on the algorithm, such as device size and nanowire separation. Once the shape is found, an electrostatic implementation is required to determine the feasibility of such result.

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